

Taiwan Semiconductor

# 20A, 35V - 200V Schottky Barrier Rectifier

#### FEATURES

- AEC-Q101 qualified available
- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

### APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

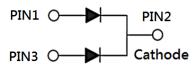
#### **MECHANICAL DATA**

- Case: ITO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.70g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I <sub>F</sub>	20	А		
V <sub>RRM</sub>	35 - 200	V		
I <sub>FSM</sub>	150	А		
T <sub>J MAX</sub>	150	°C		
Package	ITO-220AB			
Configuration	Dual dies			







<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)											
		MBRF	MBRF	MBRF							
PARAMETER	SYMBOL	2035	2045	2050	2060	2080	2090	20100	20150	20200	UNIT
		СТ	СТ	СТ							
Maril 1		MBRF	MBRF	MBRF							
Marking code on the device		2035	2045	2050	2060	2080	2090	20100	20150	20200	
the device		СТ	СТ	СТ							
Repetitive peak reverse voltage	V <sub>RRM</sub>	35	45	50	60	80	90	100	150	200	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	24	31	35	42	56	63	70	105	140	V
Forward current	I <sub>F</sub>					20					А
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>		150					A			
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1	.0				0.5				A



# MBRF2035CT – MBRF20200CT Taiwan Semiconductor

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)											
PARAMETER	SYMBOL	MBRF 2035 CT	MBRF 2045 CT	MBRF 2050 CT	MBRF 2060 CT	MBRF 2080 CT				MBRF 20200 CT	
Peak repetitive forward current (Rated $V_R$ , Square wave, 20KHz)	I <sub>FRM</sub>		20						A		
Critical rate of rise of off-state voltage	dv/dt		10,000						V/µs		
Junction temperature	TJ		-55 to +150					°C			
Storage temperature	$T_{STG}$		-55 to +150					°C			

#### Notes:

1. tp = 2.0µs, 1.0KHz

THERMAL PERFORMANCE					
PARAMETER		SYMBOL	ТҮР	UNIT	
Junction-to-case thermal	MBRF2035CT-2060CT	Р	1.5	°C/W	
resistance	MBRF2080CT-20200CT	R <sub>eJC</sub>	3.5	°C/W	

ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward voltage per diode <sup>(1)</sup>	MBRF2035CT MBRF2045CT MBRF2050CT MBRF2060CT MBRF2080CT	I <sub>F</sub> = 10A,TJ = 25°C		-	0.80	V
	MBRF2090CT MBRF20100CT			-	0.85	V
	MBRF20150CT MBRF20200CT			-	0.95	V
	MBRF2035CT MBRF2045CT		V <sub>F</sub>	-	0.84	V
	MBRF2050CT MBRF2060CT			-	0.95	V
	MBRF2080CT	$I_F = 20A, T_J = 25^{\circ}C$		-	1.00	
	MBRF2090CT MBRF20100CT			-	0.95	V
	MBRF20150CT MBRF20200CT			-	1.05	V



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PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBRF2035CT				0.57	
	MBRF2045CT			-	0.57	V
	MBRF2050CT				0.70	
	MBRF2060CT			-	0.70	V
	MBRF2080CT	I <sub>F</sub> = 10A,T <sub>J</sub> = 125°C		-	0.65	V
	MBRF2090CT				0.75	
	MBRF20100CT			-	0.75	V
	MBRF20150CT			-	0.85	V
Forward voltage per diode <sup>(1)</sup>	MBRF20200CT		N/	-	0.05	V
Forward voltage per diode	MBRF2035CT		V <sub>F</sub>	-	0.72	v
	MBRF2045CT				0.72	v
	MBRF2050CT			-	0.85	v
	MBRF2060CT	I <sub>F</sub> = 20A,T <sub>J</sub> = 125°C			0.00	v
	MBRF2080CT			-	0.75	V
	MBRF2090CT			-	0.85	V
	MBRF20100CT			-	0.85	V
	MBRF20150CT			-	0.95	v
	MBRF20200CT				0.00	v
	MBRF2035CT					
	MBRF2045CT					
	MBRF2050CT					
	MBRF2060CT					
	MBRF2080CT	$T_J = 25^{\circ}C$		-	100	μA
	MBRF2090CT					
	MBRF20100CT					
	MBRF20150CT					
Reverse current @ rated $V_R$ per			I <sub>R</sub>			
diode <sup>(2)</sup>	MBRF2035CT		٠ĸ	-	15	mA
	MBRF2045CT					
	MBRF2050CT			-	10	mA
	MBRF2060CT	T <sub>J</sub> = 125°C				
	MBRF2080CT			-	30	mA
	MBRF2090CT			-	5	mA
	MBRF20100CT					
	MBRF20150CT			-	2	mA
	MBRF20200CT					

#### Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms



# MBRF2035CT – MBRF20200CT Taiwan Semiconductor

## ORDERING INFORMATION

ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING
MBRF20xCT	ITO-220AB	50 / Tube
MBRF20xCTH	ITO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 35V(MBRF2035CT) to 200V(MBRF20200CT)

2. "H" means AEC-Q101 qualified



1000

100

10

1

0.1

0.01

0.001

10 20

**INSTANTANEOUS REVERSE CURRENT (mA)** 

## **MBRF2035CT – MBRF20200CT**

**Fig.2 Typical Junction Capacitance** 

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#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

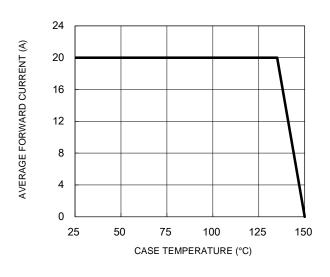


Fig.1 Forward Current Derating Curve

#### **Fig.3 Typical Reverse Characteristics**

- - -

T<sub>1</sub>=125°C

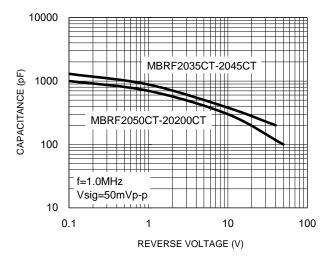
',=75°C

=25°C

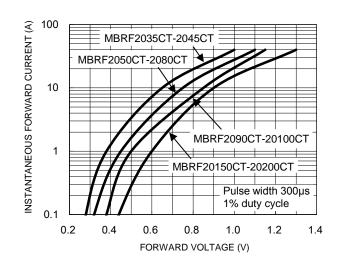
PERCENT OF RATED PEAK REVERSE VOLTAGE (%)

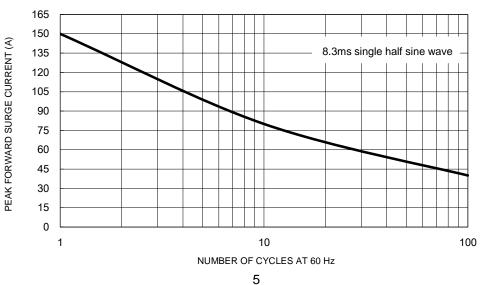
MBRF2035CT-2045CT MBRF2050CT-20200CT

> 30 40 50 60 70 80 90 100



#### **Fig.4 Typical Forward Characteristics**





#### Fig.5 Maximum Non-Repetitive Forward Surge Current

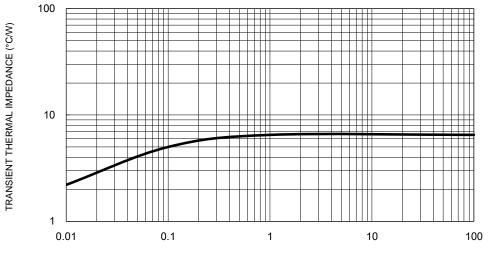
Version: O2105



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### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



#### Fig.6 Typical Transient Thermal Impedance

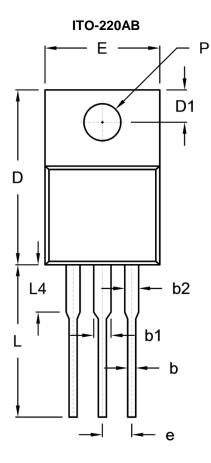
PULSE DURATION (s)

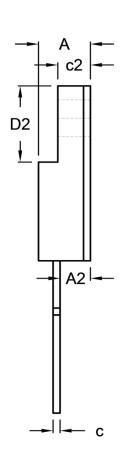


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### PACKAGE OUTLINE DIMENSIONS





DIM.	Unit	(mm)	Unit (	(inch)
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A2	2.30	2.96	0.091	0.117
b	0.50	0.90	0.020	0.035
b1	-	1.80	-	0.071
b2	0.95	1.45	0.037	0.057
с	0.46	0.76	0.018	0.030
c2	2.50	3.16	0.098	0.124
D	14.80	15.50	0.583	0.610
D1	2.40	3.20	0.094	0.126
D2	6.30	6.90	0.248	0.272
E	9.60	10.30	0.378	0.406
е	2.41	2.67	0.095	0.105
L	12.60	13.80	0.496	0.543
L4	-	4.10	-	0.161
Р	3.00	3.40	0.118	0.134

#### **MARKING DIAGRAM**

雪別 GYWW <mark>F</mark>
P/N
<b>→</b> + • • •

P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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